

Effects of Al addition to Si-based flux on the growth of 4H-SiC films by vapour-liquid-solid pulsed laser deposition

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Supporting information

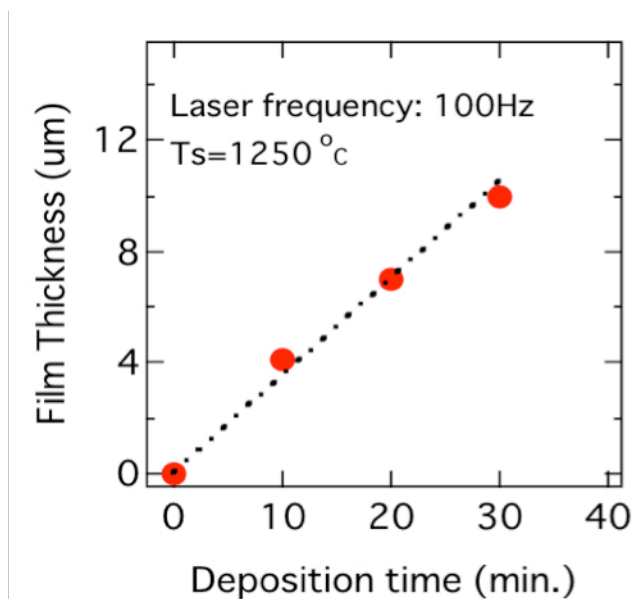


Figure S1. The thickness of SiC films plotted as a function of deposition time. A good linear relationship between them gives a VLS growth rate of $\sim 25\mu\text{m/h}$ in average under the present deposition conditions.

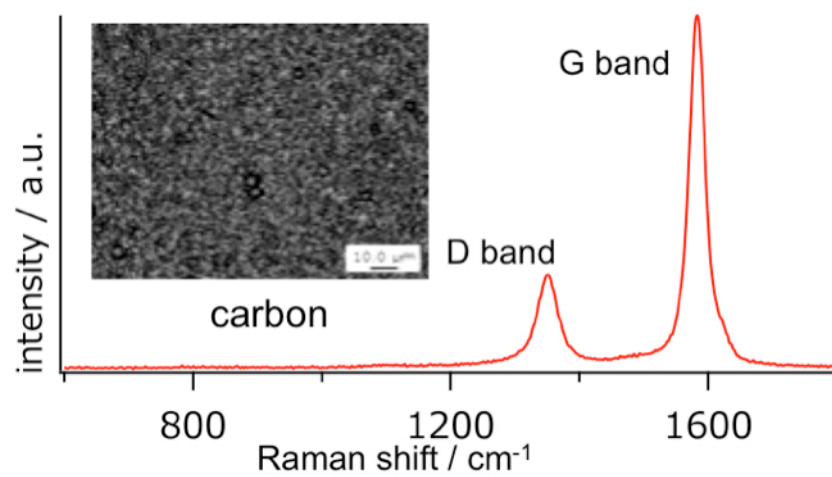


Figure S2. A typical Raman spectrum for a film obtained by depositing SIC without flux at 1250 °C, along with its SEM image (inset).